Abstract of the Disclosure

An inspection method and apparatus irradiates a sample on which a pattern is formed with an electron beam, so that an inspection image and a reference image can be generated on the basis of a secondary electron or a reflected electron emitted by the sample. An abnormal pattern is determined based on a difference in halftone values of each pixel between the inspection image and the reference image. A plurality of feature quantities of the abnormal pattern are obtained from an image of the abnormal pattern, and, based on the distribution of the plurality of feature quantities of the abnormal pattern, a range for classifying the type of the abnormal pattern is designated. Thus, a desired defect can be extracted from many defects extracted by inspection.